

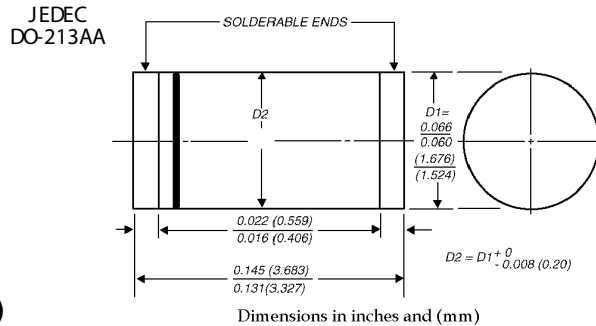
Mechanical Dimension

SD103AMM~CMM

Description



GLASS MINIMELF(DO-213AA)



FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$

Parameter	Symbol	SD103AMM	SD103BMM	SD103CMM	Unit
Peak Repetitive Peak reverse voltage Working Peak	V_{RRM}				
DC Blocking Voltage	V_{RWM}	40	30	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Repetitive Peak Forward Current @ $t \leq 1.0\text{s}$	I_{FRM}	1.0			A
Power Dissipation	P_d	400			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	250			$^\circ\text{C/W}$
Storage temperature	T_{STG}	-65~+175			$^\circ\text{C}$

Electrical Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$				V	$I_R=10\mu\text{A}$
SD103AMM		40				
SD103BMM		30				
SD103CMM		20				
Forward voltage	V_F			0.37 0.60	V	$I_F=20\text{mA}$ $I_F=200\text{mA}$
Reverse current	I_{RM}			5.0	μA	$V_R=30\text{V}$ $V_R=20\text{V}$ $V_R=10\text{V}$
Capacitance between terminals	C_T		50		pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}		10		ns	$I_F=I_R=50\sim 200\text{mA}$ $I_{rr}=0.1I_R, R_L=100\Omega$

Typical Characteristics SD103AMM-SD103CMM

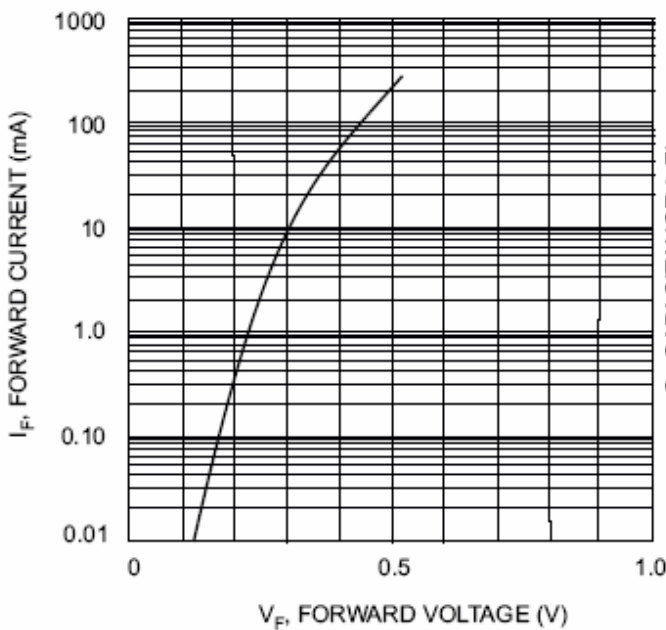


Fig. 1 Typical Forward Characteristics

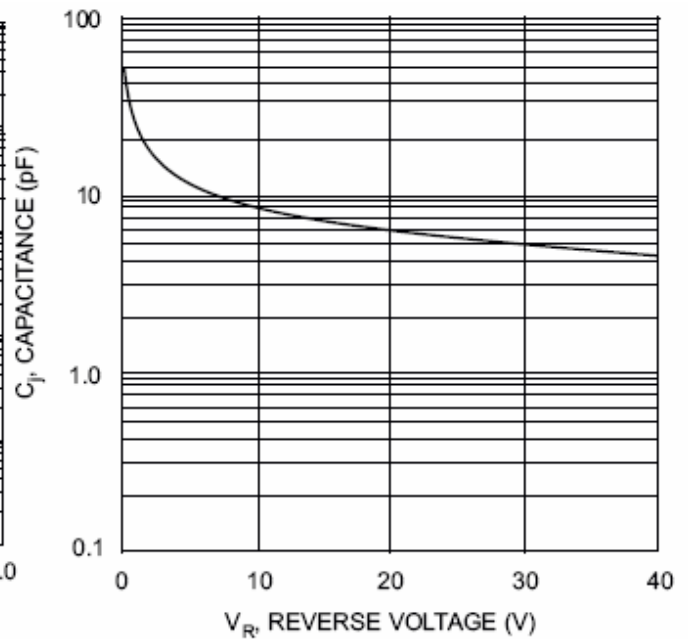


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

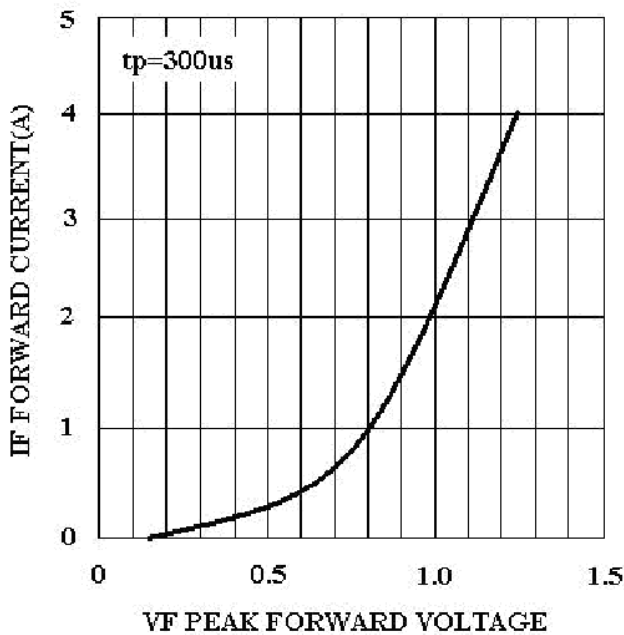


Fig. 3 TYPICAL HIGH CURRENT FORWARD

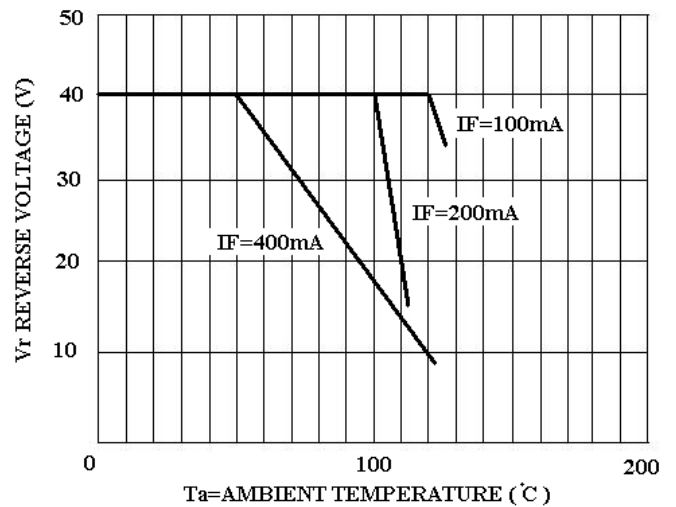


Fig 4 BLOCKING VOLTAGE DERATING CURVES